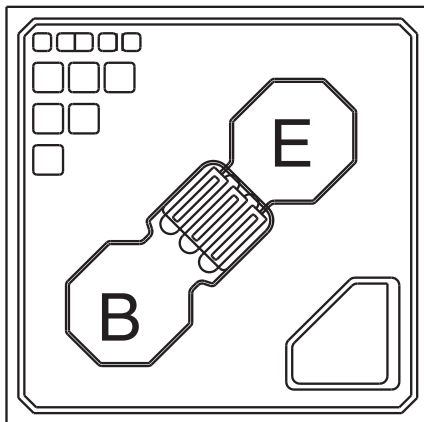


PROCESS DETAILS

| | |
|--------------------------|------------------|
| Process | EPITAXIAL PLANAR |
| Die Size | 16 x 16 MILS |
| Die Thickness | 8.0 MILS |
| Base Bonding Pad Area | 3.75 x 3.75 MILS |
| Emitter Bonding Pad Area | 3.75 x 3.75 MILS |
| Top Side Metalization | Al - 30,000Å |
| Back Side Metalization | Au - 10,000Å |

GEOMETRY



BACKSIDE COLLECTOR R0

GROSS DIE PER 4 INCH WAFER

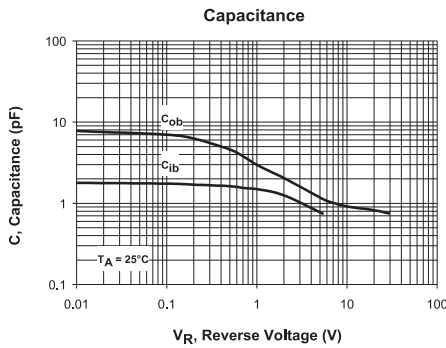
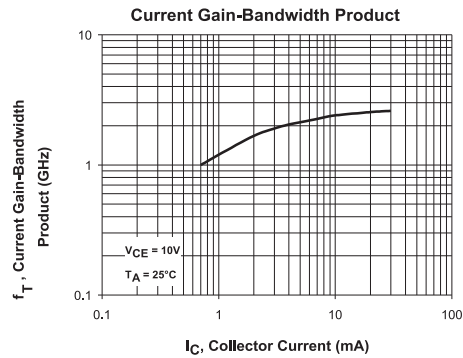
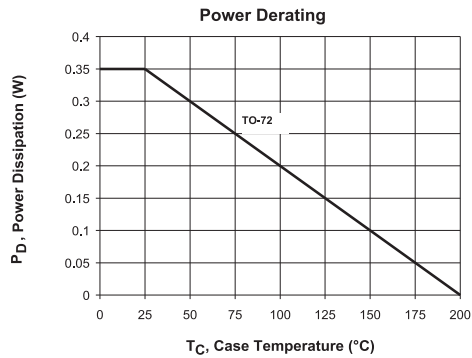
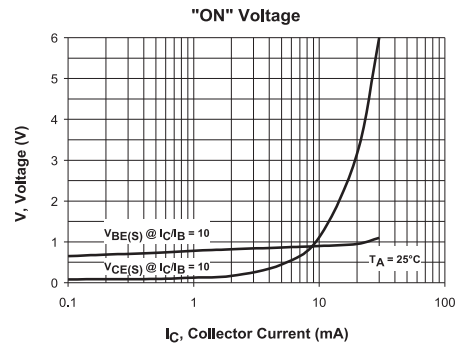
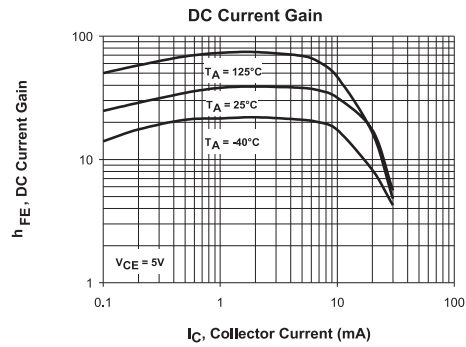
44,140

PRINCIPAL DEVICE TYPES

CM4957

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R2 (1-August 2002)



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